

TYPES 1N914, 1N914A, 1N914B, 1N915, 1N916, 1N916A, 1N916B, 1N917 SILICON SWITCHING DIODES

BULLETIN NO. DL-S 7311954, MARCH 1973

FAST SWITCHING DIODES

- Rugged Double-Plug Construction

Electrical Equivalents

1N914 ... 1N4148 ... 1N4531

1N914A ... 1N4446

1N914B ... 1N4448

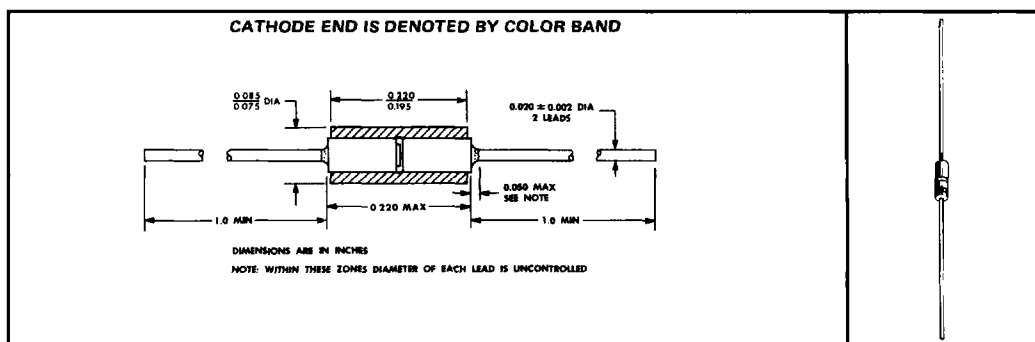
1N916 ... 1N4149

1N916A ... 1N4447

1N916B ... 1N4449

mechanical data

Double-plug construction affords integral positive contacts by means of a thermal compression bond. Moisture-free stability is ensured through hermetic sealing. The coefficients of thermal expansion of the glass case and the dumet plugs are closely matched to allow extreme temperature excursions. Hot-solder-dipped leads are standard.



absolute maximum ratings at specified free-air temperature

	1N914 1N914A 1N914B	1N915	1N916 1N916A 1N916B	1N917	UNIT
Working Peak Reverse Voltage from -65°C to 150°C	75*	50*	75*	30*	V
Average Rectified Forward Current (See Note 1)	at (or below) 25°C 10*	75* 10*	75* 10*	50* 10*	mA
Peak Surge Current, 1 Second at 25°C (See Note 2)	500*	500	500*	300	mA
Continuous Power Dissipation at (or below) 25°C (See Note 3)	250*	250	250*	250	mW
Operating Free-Air Temperature Range	-65 to 175				°C
Storage Temperature Range	-65 to 200*				°C
Lead Temperature 1/16 Inch from Case for 10 Seconds	300				°C

NOTES: 1. These values may be applied continuously under a single-phase 60-Hz half-sine-wave operation with resistive load.
2. These values apply for a one-second square-wave pulse with the devices at nonoperating thermal equilibrium immediately prior to the surge.
3. Derate linearly to 175°C free-air temperature at the rate of 1.67 mW/°C.

*JEDEC registered data

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TYPES 1N914, 1N914A, 1N914B, 1N915, 1N916, 1N916A, 1N916B, 1N917

SILICON SWITCHING DIODES

1N914 SERIES AND 1N915

*electrical characteristics at 25°C free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	1N914		1N914A		1N914B		1N915		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
$V_{(BR)}$ Reverse Breakdown Voltage	$I_R = 100 \mu A$	100		100		100		65		V
I_R Static Reverse Current	$V_R = 10 V$							25		nA
	$V_R = 20 V$		25		25		25			
	$V_R = 20 V, T_A = 100^\circ C$						3		5	μA
	$V_R = 20 V, T_A = 150^\circ C$		50		50		50			
	$V_R = 50 V$								5	
	$V_R = 75 V$		5		5		5			
V_F Static Forward Voltage	$I_F = 5 mA$					0.62	0.72	0.6	0.73	V
	$I_F = 10 mA$		1							
	$I_F = 20 mA$				1					
	$I_F = 50 mA$								1	
	$I_F = 100 mA$						1			
C_T Total Capacitance	$V_R = 0, f = 1 MHz$		4		4		4		4	pF

1N916 SERIES AND 1N917

*electrical characteristics at 25°C free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	1N916		1N916A		1N916B		1N917		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
$V_{(BR)}$ Reverse Breakdown Voltage	$I_R = 100 \mu A$	100		100		100		40		V
I_R Static Reverse Current	$V_R = 10 V$							50		nA
	$V_R = 20 V$		25		25		25			
	$V_R = 20 V, T_A = 100^\circ C$						3		25	μA
	$V_R = 20 V, T_A = 150^\circ C$		50		50		50			
	$V_R = 75 V$		5		5		5			
V_F Static Forward Voltage	$I_F = 0.25 mA$							0.64		V
	$I_F = 1.5 mA$							0.74		
	$I_F = 3.5 mA$							0.83		
	$I_F = 5 mA$					0.63	0.73			
	$I_F = 10 mA$		1						1	
	$I_F = 20 mA$				1					
	$I_F = 30 mA$						1			
C_T Total Capacitance	$V_R = 0, f = 1 MHz$		2		2		2		2.5	pF

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NOTE 4: These parameters must be measured using pulse techniques. $t_W = 300 \mu s$, duty cycle $\leq 2\%$.

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TYPES 1N914, 1N914A, 1N914B, 1N915, 1N916, 1N916A, 1N916B, 1N917 SILICON SWITCHING DIODES

operating characteristics at 25°C free-air temperature

PARAMETER	TEST CONDITIONS	1N914 1N914A 1N914B 1N916 1N916A 1N916B	1N915	1N917	UNIT
		MIN MAX	MIN MAX	MIN MAX	
t_{rr} Reverse Recovery Time	$I_F = 10 \text{ mA}$, $I_{RM} = 10 \text{ mA}$, $i_{rr} = 1 \text{ mA}$, $R_L = 100 \Omega$, See Figure 1 (Condition 1)	8	10*	3*	ns
	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $i_{rr} = 1 \text{ mA}$, $R_L = 100 \Omega$, See Figure 1 (Condition 2)	4*			ns
$V_{FM(rec)}$ Forward Recovery Voltage	$I_F = 50 \text{ mA}$, $R_L = 50 \Omega$, See Figure 2	2.5*			V
η_r Rectification Efficiency	$V_r = 2 \text{ V}$, $R_L = 5 \text{ k}\Omega$, $C_L = 20 \text{ pF}$, $Z_{source} = 50 \Omega$, $f = 100 \text{ MHz}$	45*			%

PARAMETER MEASUREMENT INFORMATION

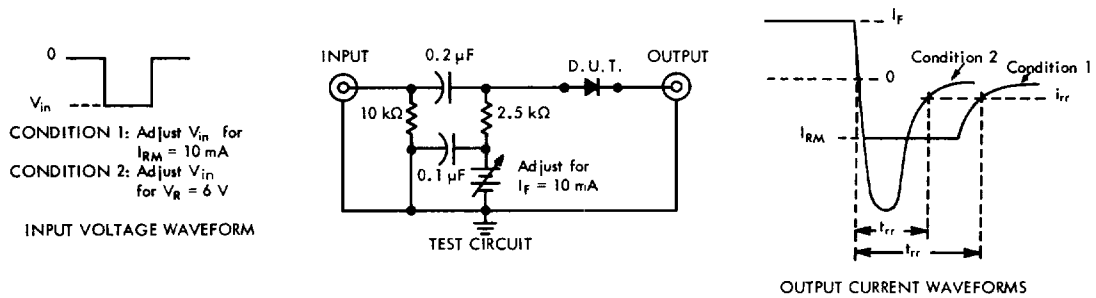


FIGURE 1 — REVERSE RECOVERY TIME

NOTES: a. The input pulse is supplied by a generator with the following characteristics: $Z_{out} = 50 \Omega$, $t_r \leq 0.5 \text{ ns}$, $t_w = 100 \text{ ns}$.
b. Output waveforms are monitored on an oscilloscope with the following characteristics: $t_r \leq 0.6 \text{ ns}$, $Z_{in} = 50 \Omega$.

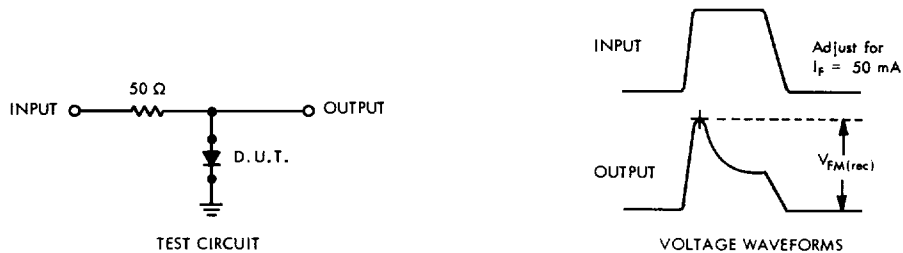


FIGURE 2 — FORWARD RECOVERY VOLTAGE

NOTES: c. The input pulse is supplied by a generator with the following characteristics: $Z_{out} = 50 \Omega$, $t_r \leq 30 \text{ ns}$, $t_w = 100 \text{ ns}$, $PRR = 5 \text{ to } 100 \text{ kHz}$.
d. The output waveform is monitored on an oscilloscope with the following characteristics: $t_r \leq 15 \text{ ns}$, $R_{in} \geq 1 \text{ M}\Omega$, $C_{in} \leq 5 \text{ pF}$.

* JEDEC registered data